

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application:

1. (Currently amended): A method of generating ions, comprising:

heating an ion source material composed of indium iodide (InI) and having a particle size larger than 1 mm and not larger than 5 mm ~~at a temperature of not lower than 275°C and not higher than 380°C~~ to generate a vapor of said indium iodide (InI);
and

generating indium (In) ions by discharging said vapor, ~~to produce an ion beam current of not less than 2μA.~~

2-4. (Canceled):

5. (Currently amended): A method of irradiating ions, comprising:

heating an ion source material composed of indium iodide (InI) and having a particle size larger than 1 mm and not larger than 5 mm ~~at a temperature of not lower than 275°C and not higher than 380°C~~ to generate a vapor of said indium iodide (InI);
[[and]]

generating indium (In) ions by discharging said vapor, ~~to produce an ion beam current of not less than 2μA;~~ and

selectively irradiating said indium (In) ions onto a substrate to be processed.

6-20. (Canceled):

21. (Currently amended): The method according to claim 1, wherein said heating an ion source material comprises heating said indium iodide (InI) at a temperature of not lower than [[300]] 275 °C and not higher than 380°C to generate said vapor of said indium iodide (InI).

22-28. (Canceled):

29. (New): The method according to claim 1, wherein said heating an ion source material includes supplying said indium iodide into an oven which has an outlet nozzle for said vapor, followed by heating said indium iodide whose particle size is larger than a diameter of said outlet nozzle.

30. (New): The method according to claim 1, wherein, in said step of generating indium (In) ions by discharging said vapor, a support gas inlet to an arc chamber and a vapor inlet to said arc chamber are provided on one face of said arc chamber, and are configured to introduce support gas and said vapor into said arc chamber.

31. (New): A method of generating ions, comprising:

heating an ion source material composed of indium iodide (InI) which is supplied in an oven having a vapor outlet nozzle and whose particle size is larger than a diameter of said outlet nozzle; and

generating indium (In) ions by discharging said vapor.

32. (New): The method according to claim 31, wherein said heating an ion source material includes heating said indium iodide at a temperature of not lower than 275°C and not higher than 380°C.

33. (New): The method according to claim 31, wherein, in said step of generating indium (In) ions by discharging said vapor, a support gas inlet to an arc chamber and a vapor inlet to said arc chamber are provided on one face of said arc chamber, and are configured to introduce support gas and said vapor generated into said arc chamber.

34. (New): A method of irradiating ions, comprising:

heating an ion source material composed of indium iodide (InI) which is supplied in an oven having a vapor outlet nozzle and whose particle size is larger than a diameter of said outlet nozzle;

generating indium (In) ions by discharging said vapor; and

selectively irradiating said indium (In) ions onto a substrate to be processed.

35. (New): A method of generating ions, comprising:

heating an ion source material composed of indium iodide (InI) to generate a vapor of said indium iodide (InI); and

generating indium (In) ions by discharging said vapor in an arc chamber in which a support gas inlet to said arc chamber and a vapor inlet to said arc chamber are provided on one face of the arc chamber, and are configured to introduce support gas and said vapor generated into said chamber.

36. (New): The method according to claim 35, wherein a filament is provided on a first side surface of said arc chamber, and a reflecting counter electrode is provided on a second side surface of said arc chamber opposite to said first side surface, and said one face where said support gas inlet and said vapor inlet are provided is between said first and said second side surfaces and perpendicular thereto.

37. (New): A method of irradiating ions, comprising:

heating an ion source material composed of indium iodide (InI) to generate a vapor of said indium iodide (InI);

generating indium (In) ions by discharging said vapor in an arc chamber in which a support gas inlet to said arc chamber and a vapor inlet to said arc chamber are provided on one face of the arc chamber, and are configured to introduce support gas and said vapor generated into said chamber; and

selectively irradiating said indium (In) ions onto a substrate to be processed.